

品 名 Model Type	Nano SIM Socket Dual Tray Type
料 號 Part No.	KMCX1NSM640541
客戶料號 Customer Part No.	

ISSUE	DATE	WRTN	CHKD	APVD	DESCRIPTIONS
	2023.08.18	李阮龍	李阮龍	郭遠峰	New Release

TITLE	SPC. NO.	DATE	Version
Nano SIM Socket Dual Tray		2023.08.18	001
Туре	KMCX1NSM640541		

1. SCOPE

1.1. CONTENTS

This specification covers the performance, tests and quality requirements for the Nano SIM Connector, P/N : KMCX1NSM640541

2. APPLICABLE DOCUMENT

The following Kunming documents form a part of this specification to the extent specified herein. Unless otherwise specified, the latest edition of the document applies. In the event of conflict between the requirements of this specification and the product drawing, the product drawing shall take precedence. In the event of conflict between the requirements of this specification and the referenced documents, this specification shall take precedence.

3. REQUIREMENTS

3.1. DESIGN AND CONSTRUCTION

Product shall be of the design, construction and physical dimensions specified on the applicable product drawing.

3.2. MATERIALS

Refer to Kunming Product Drawing

3.3. RATINGS

- A. Voltage Rating : 50V Max.
- B. Current Rating : 0.5A
- C. Temperature : -40°C ~ +85°C

3.4. PERFOMANCE REQUEIREMENT AND TEST DESCRIPTION

The product shall be designed to meet the electrical, mechanical and environmental performance requirements specified in "4. TEST METHOD AND PERFPRMANCE".

4. TEST METHOD AND PERFORMANCE

4.1. INDUSTRY STANDARDS

Unless otherwise specified, all tests and measurement should be performed under the following conditions in accordance with EIA-364 : Electrical Connector/Socket Test Procedures Including Environmental Classifications

TITLE	SPC. NO.	DATE	Version
Nano SIM Socket Dual Tray		2023.08.18	001
Туре	KMCX1NSM640541		

4.2. TEST CONDITION

Temperature : 15°C ~35°C

Humidity : 45% ~ 75% RH.

Atmospheric Pressure : 86 ~ 106 kPa

	4-3 APPEARANCE CHECK							
	TEST ITEM	REQUIREMENT	PROCEDURE					
4-3-1	Appearance t	Must comply with product drawing.	Inspect and measure the contact.					
		4-4 ELECTRICAL REQUI	REMENT					
4-4-1	Contact Resistance	100 mΩ max.	Subject mated contacts assembled in housing to 20mV Max open circuit at 10mA Max. EIA-364-6B					
4-4-2	Dielectric Withstanding Voltage	No evidence of flash over or insulation shall take place. Current leakage:0.5mA Max.	500V AC for 1 minute. Test between adjacent circuits of unmated connector. EIA-364-20B					
4-4-3	Insulation Resistance	1000 MΩ Min.	Impressed voltage 500V DC. Test between adjacent circuits of unmated connector. EIA-364-21C					
	4	-5 MECHANICAL REQU	IREMENT					
4-5-1	Insert Force	10N Max.	Insert Nano SIM Card into the holder and make it work, at a rate of 25.4mm per minute. EIA-364-13B					
4-5-2	Unmating Force	0.5N Min.	Push out the working nano Sim Card from the holder, at rate of 25.4mm per minute					

TITLE	SPC. NO.	DATE	Version
Nano SIM Socket Dual Tray		2023.08.18	001
Туре	KMCX1NSM640541		

4-5-3	Ejection Force	15N Max	Push out the Nano SIM tray form holder
4-5-4	Normal Force	30g Min.	Operation Speed : 25+3 mm/min. Measure the force required to mate connector.
4-5-5	Durability	See Note	Operation Speed : 10 cycle/min. Durability Cycles : 5000 Cycles
4-5-6	Vibration	No electrical discontinuity greater than 0.1 or 1µsec shall occur. See Note	Subject mated connectors to 10-55-10 Hz traversed in 1minutes at 1.52mm amplitude 2 Hours each of 3 mutually perpendicular planes. 100mA Max. EIA-364-28D
4-5-7	Mechanical Shock	No electrical discontinuity greater than 0.1 or 1µsec shall occur. See Note	Accelerate Velocity : 490m/s2 (50G) Waveform : Half-sine shock plus Duration : 11msec No. of Drops : 3 drops each to normal and reversed directions of X,Y and Z axes, totally 18 drops, passing DC 1mA current during the test. EIA-364-27B
	4-6	ENVIRONMENTAL REQ	UIREMENTS
		Wet solder coverage : 95%	Solder Temperature : 245+/-5°C

TITLE	SPC. NO.	DATE	Version
Nano SIM Socket Dual Tray		2023.08.18	001
Туре	KMCX1NSM640541		

4-6-3	Thermal Shock	See Note	Mated Connector -55+/-3°C (30 minutes) +85+/-2°C (30 minutes) Perform this a cycle, repeat 10cycles EIA-364-32C		
4-6-4	Humidity- Temperature Cycle	See Note	Mated Connector 25~65°C , 90~95% RH, 10 Cycles EIA-364-31B.		
4-6-5	Temperature Life (Heat Aging)	See Note	Mated Connector 85°C , 96 hours, EIA-364-17B.		
4-6-6	Salt Spray	No detrimental corrosion allowed in contact area	Subject mated connectors to 35+/-2°C and 5+/-1% salt condition for 24hours. After test, rise the sample with water and recondition the room temperature for 1 hour. EIA-364-26B.		

NOTE : Shall meet visual requirements, show no physical damage, and meet requirement of additional tests as specified in the test sequence in 4.7 test sequence.

Soldering condition shelf life about

Soldering condition shelf life about 6 months depend on storage condition of humidity, temperature and others factors.

TITLE	SPC. NO.	DATE	Version
Nano SIM Socket Dual Tray		2023.08.18	001
Туре	KMCX1NSM640541		

4.7. TEST SEQUENCE

		Test Group							
	Test or Examination	Α	В	С	D	Е	F	G	
			Test Sequence (a)						
1	Examination of Product	1,17	1,7	1,11	1,5	1,3	1,3	1,3	
2	Contact Resistance	2,10	2,4,6	2,6,8	2,4				
3	Withstanding Voltage	4,12		4,10					
4	Insulation Resistance	3,11		3,9					
5	Insert Force	5,13							
6	Unmating Force	6,14							
7	Ejection Force	7,15							
8	Normal Force	8,16							
9	Durability	9							
10	Vibration		3						
11	Mechanical Shock		5						
12	Solder Ability						2		
13	Resistance to Soldering Heat							2	
14	Thermal Shock			5					
15	Humidity Temperature Cycling			7					
16	Temperature Life (Heat Aging)				3				
17	Salt Spray					2			
	Quantities of Samples	5	5	5	5	5	5	5	

NOTE 2 :

• Numbers indicate sequence in which tests are performed.

• Discontinuities shall not take place in this test group, during tests.



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